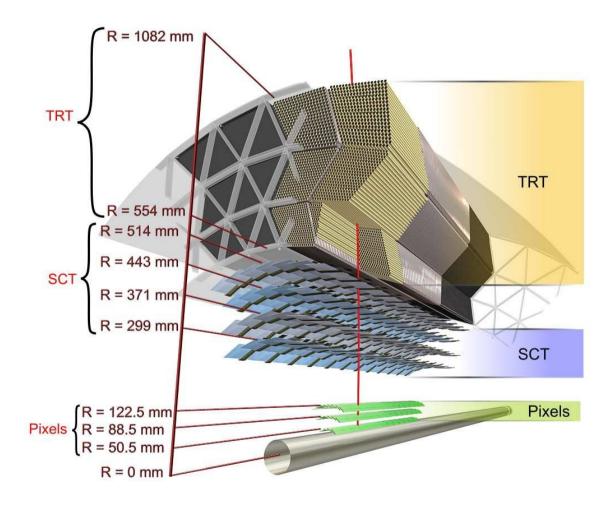
# TRACKING DETECTORS

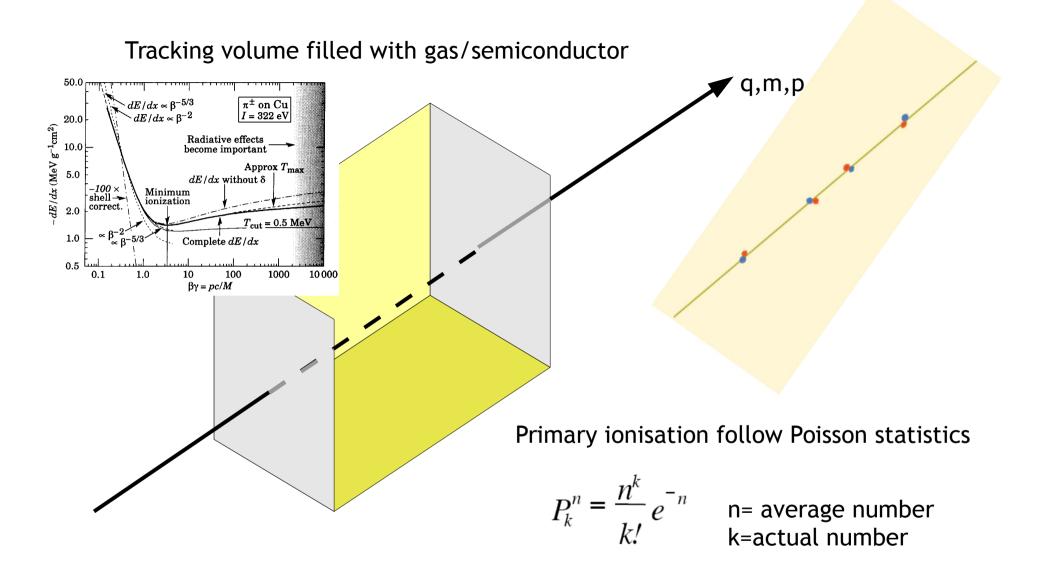


# Lecture 1

# Basic considerations and gaseous detectors

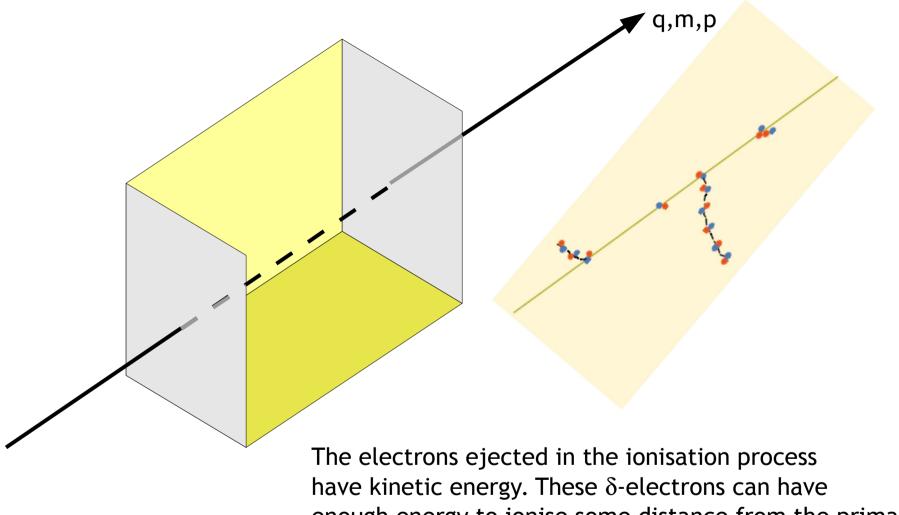
Parts of this lecture taken from lectures given by Fabio Sauli at

#### RADIATION DETECTION AND MEASUREMENT Prof. Glenn Knoll, organizer Short Courses November 10-11 2002 IEEE NSS/MIC Norfolk, November 10-16, 2002



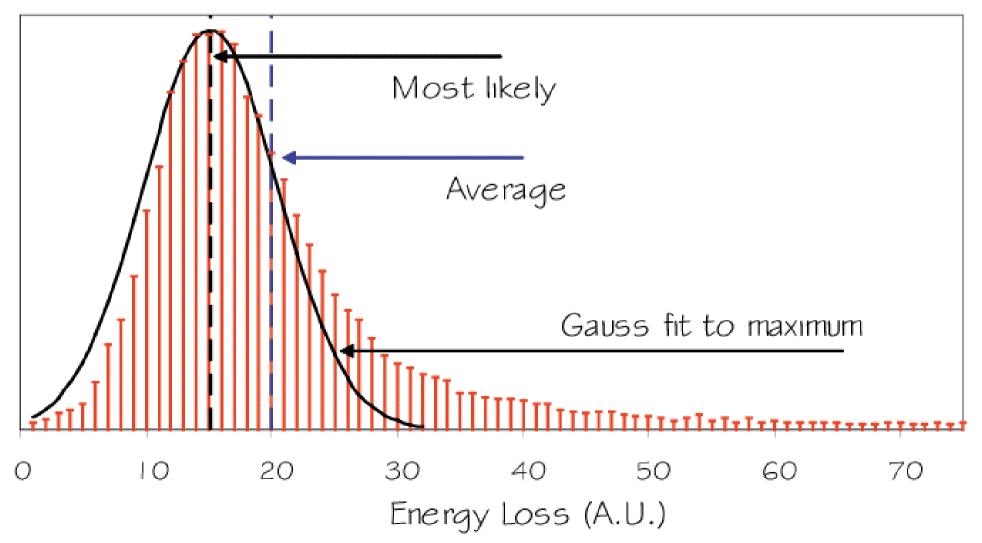
GAS (STP)	Helium	Argon	Xenon	CH4	DME	SI	Ge
dE/ dx (keV/ cm)	0.32	2.4	6.7	1.5	3.9	3870000	8830000
n (ion pairs/ cm)	6	25	44	16	55	~1E6	~3E6

NOTE: Signal in gas detector is too small to be directly read out with amplifier. The thermal noise (kT) in the amplifier is higher!



have kinetic energy. These  $\delta$ -electrons can have enough energy to ionise some distance from the primary ionisation. The total number of ionisations is approx. **3X** the number of primary ionisations. A large number of measurements lead to a distribution with a long tail towards high energy loss- the Landau fluctuation

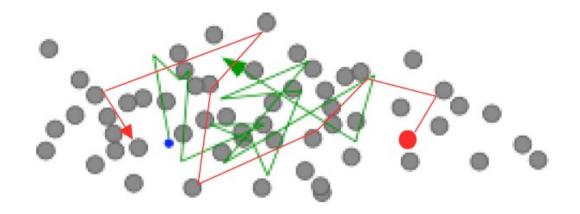
$$f(\lambda) = \sqrt{\frac{e^{-(\lambda + e^{-\kappa})}}{2\pi}}$$



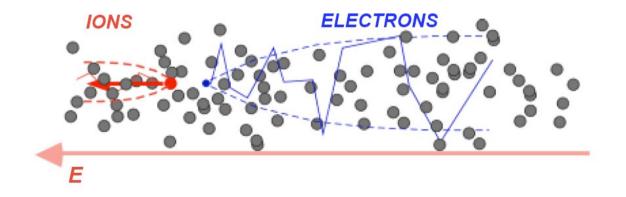
# Some more considerations on detecting charge

• • • • • • • • • •

Without electric field in the tracking volume the charge created by the ionisation will diffuse



With electric field the charge (ions and electrons) will drift

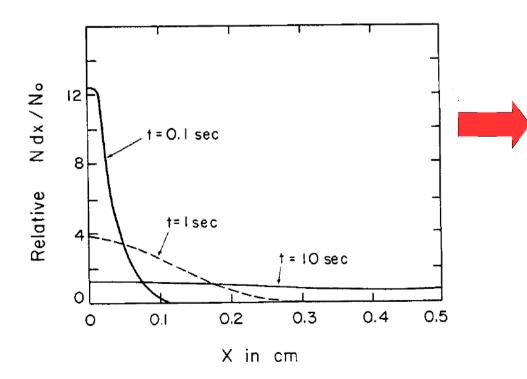


Diffusion equation gives the fraction of ions at a distance x at a given time t

$$\frac{dN}{N} = \frac{1}{\sqrt{4Dt}} e^{-\frac{x^2}{4Dt}} dx$$

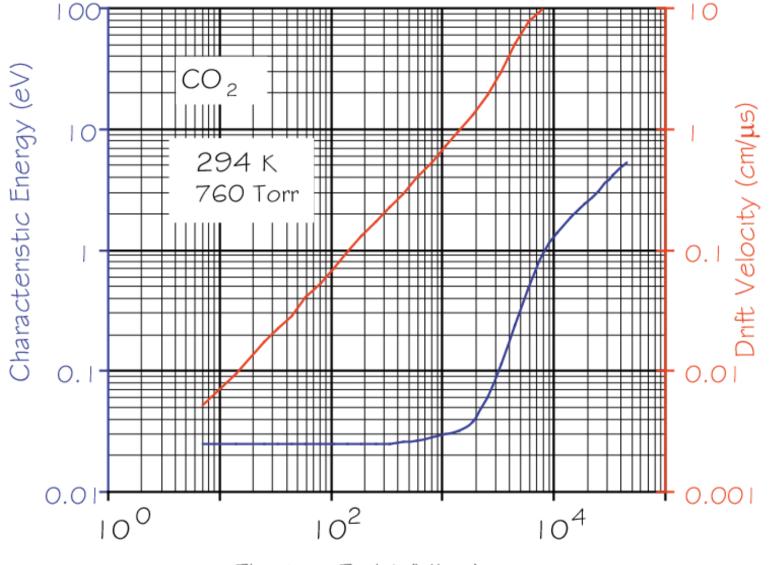
,where D is the diffusion coefficient

The RMS for linear diffusion is 
$$\sigma_x = \sqrt{2Dt}$$



Diffusion is not very efficient for charge transport ....but an enemy for charge collection

#### Drift of electrons in an electric field

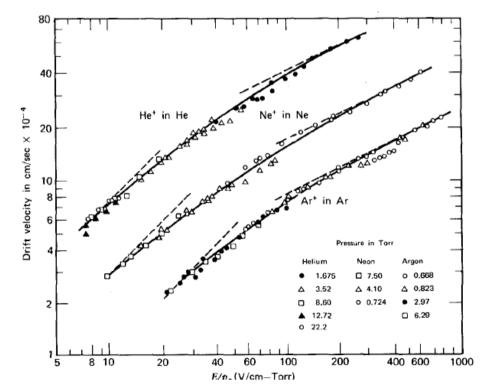


Electric Field (V/cm)

Drift of positive ions is much slower than electrons. In  $CO_2$  the difference is about 1000 The drift speed is almost linear with the electric field.

$$v_{ion} = \mu_{ion} \times E$$

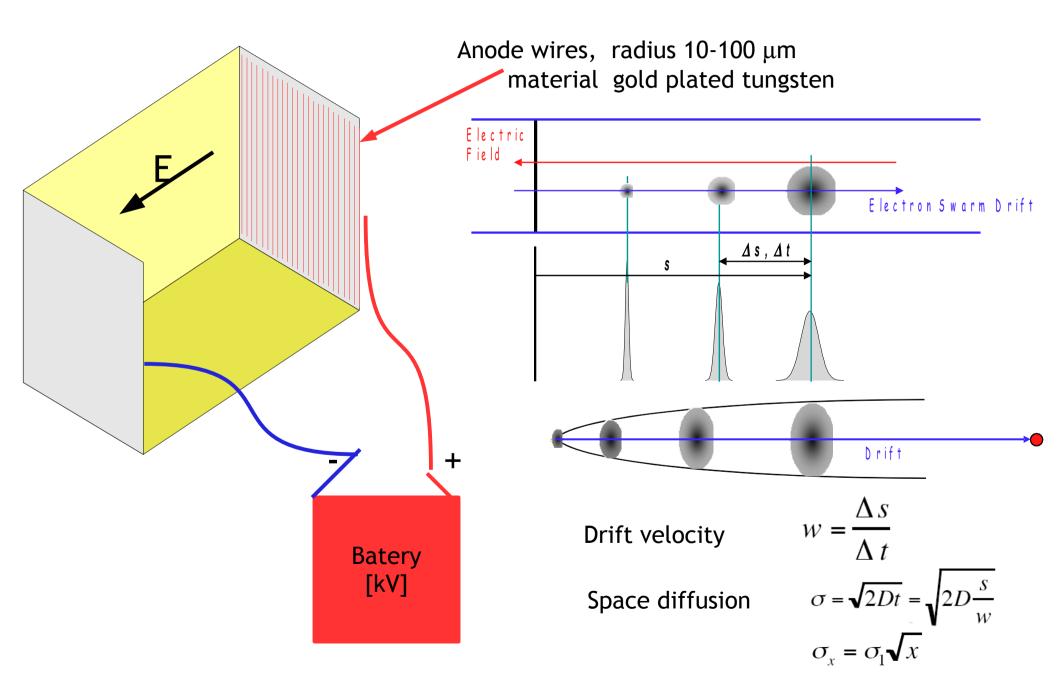
GAS	ION	µ⁺ (cm² V⁻¹ s⁻¹) @STP
Ar	Ar <sup>+</sup>	1.51
CH <sub>4</sub>	$CH_4^+$	2.26
Ar-CH <sub>4</sub> 80-20	$CH_4^+$	1.61



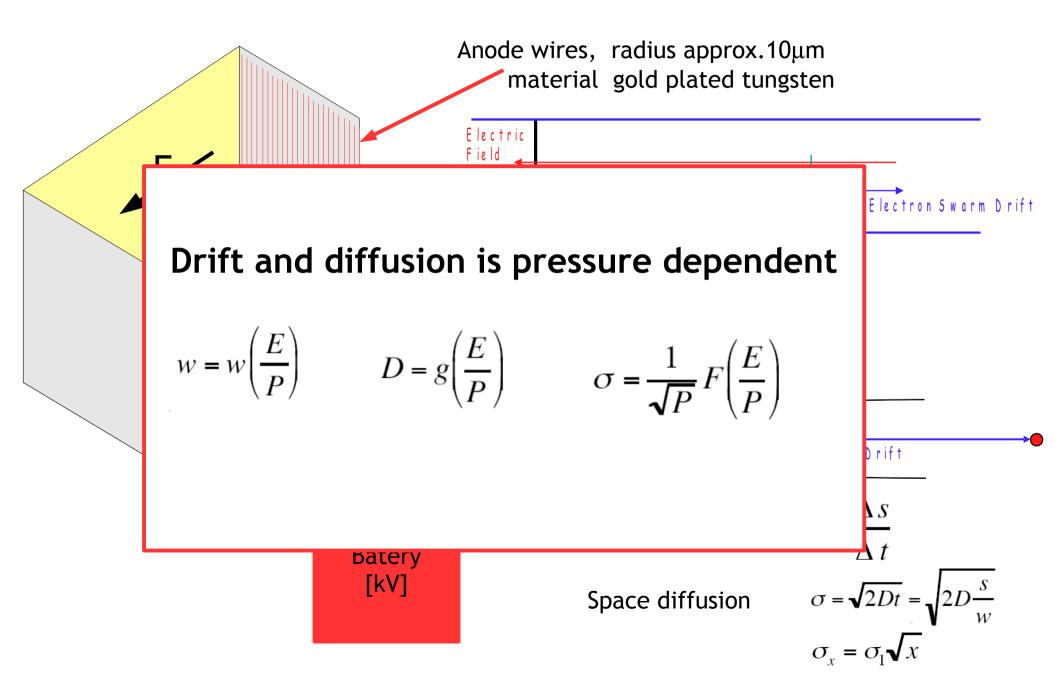
# Now lets build a gas filled detector

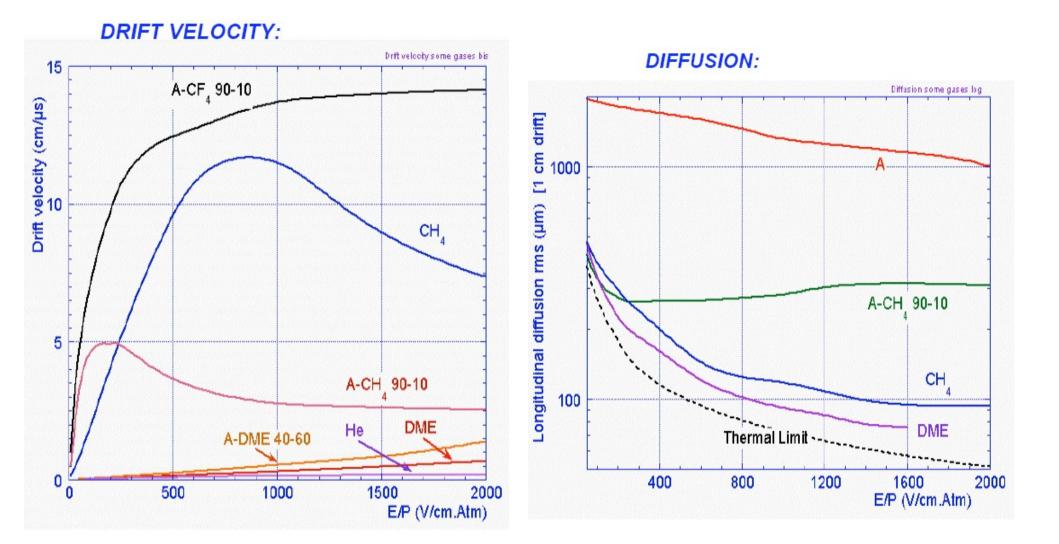
• • • • • • • • • •

## Build a wire chamber



## Build a wire chamber

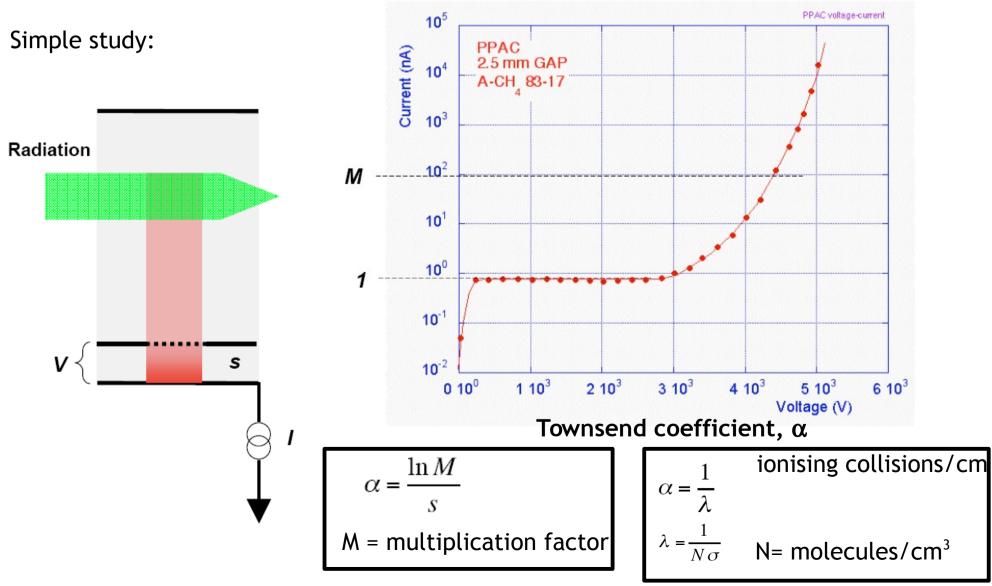


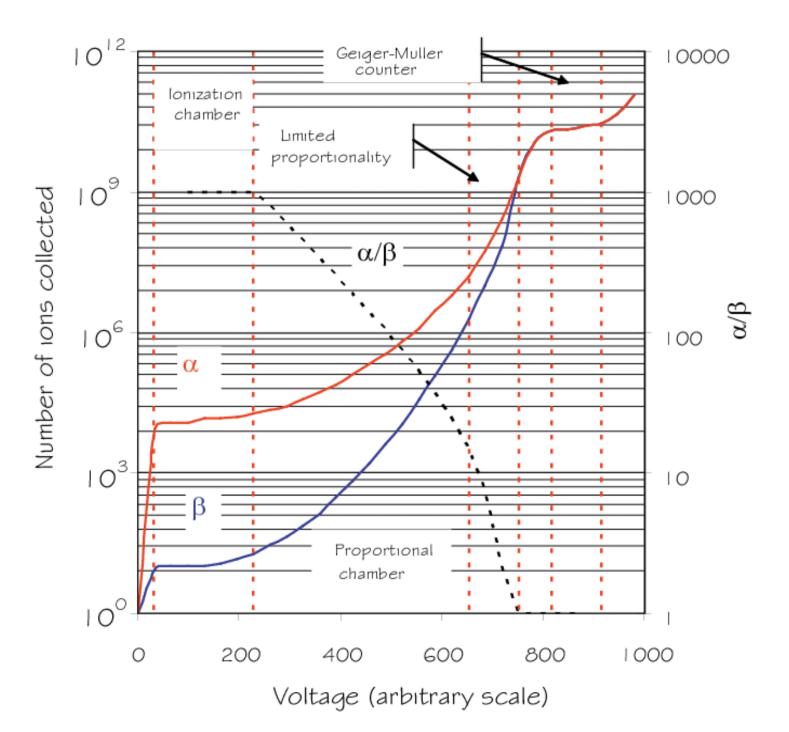


## Gas amplification and saturation effects in gaseous detectors

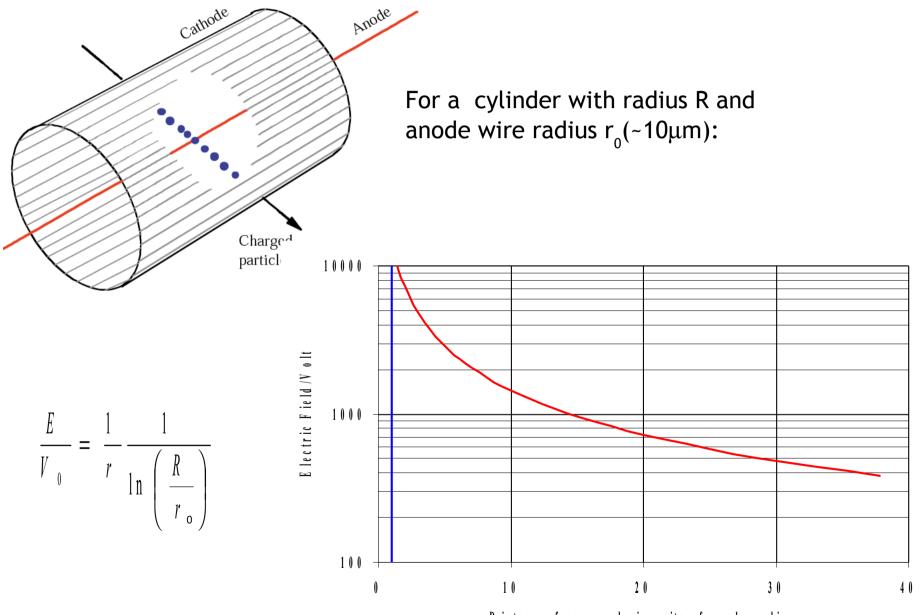
• When the electrical field is increased in the detector the kinetic energy of the drifting electrons increase

• The electrons with kinetic energy will collide creating new free electrons and ions

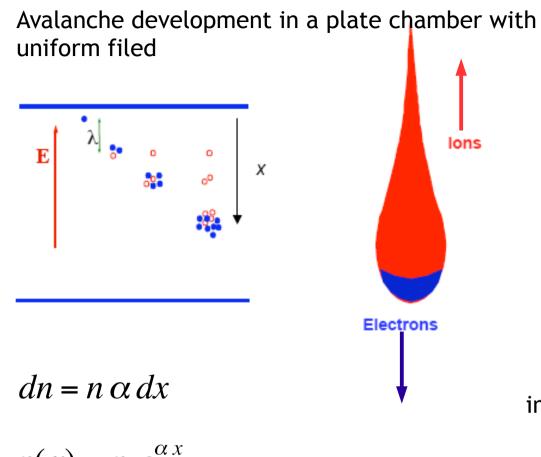


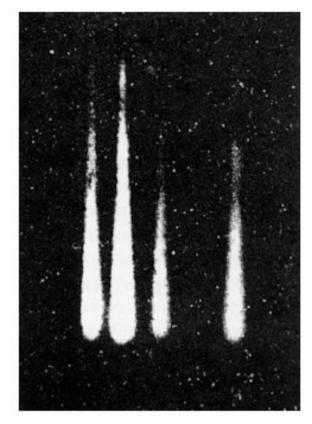


High field is also developed near the anode wire-for a simple geometry e.g. a straw tube



D is tance from anode in units of anode radius





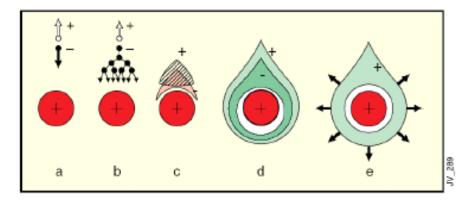
#### image from cloud-avalanche chamber

 $n(x) = n_0 e^{\alpha x}$ 

Multiplication factor (gain)

$$M(x) = \frac{n}{n_0} = e^{\alpha x}$$

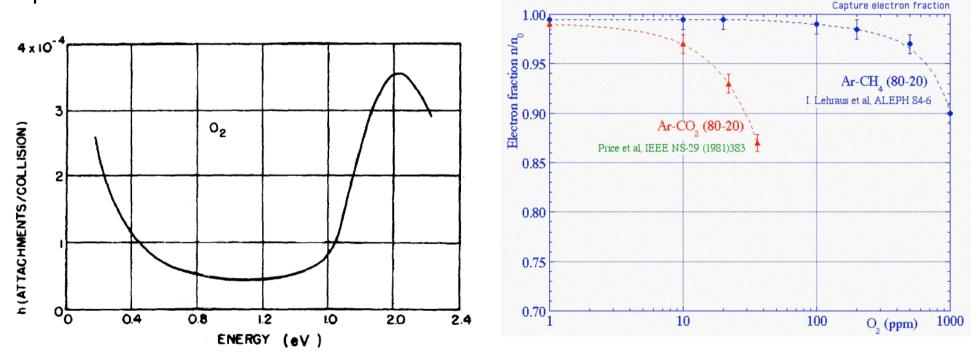
Development of avalanche close to the anode wire



## Quenching

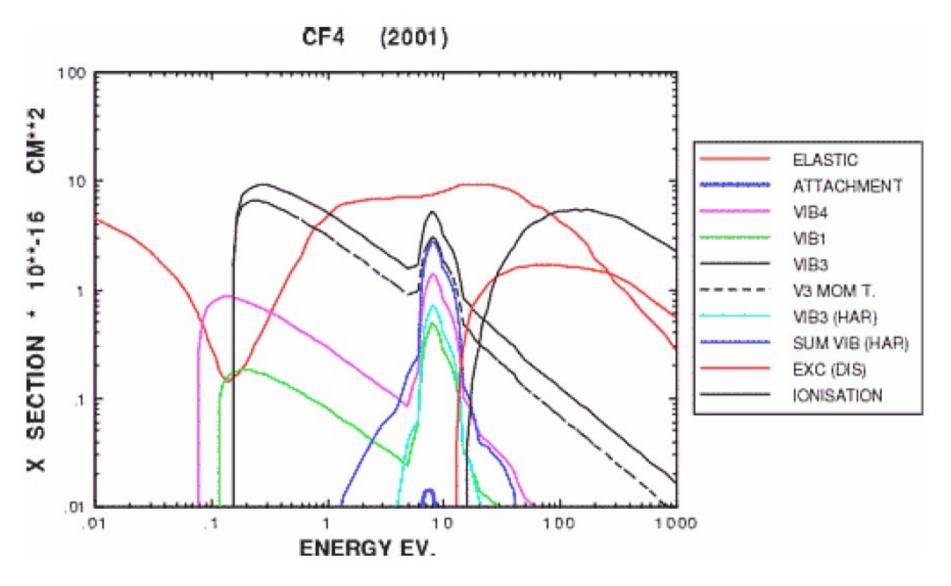
1: To get a stable behavior over a large range of particle rates and ionisation levels a quenching gas is added. The gas should have a large electron capture cross- section for energetic electrons to not let the avalanches to grow enormous and a low cross-section for thermal electrons.

2: An other problem is that noble gases emit photons above the ionisation threshold of other molecules. Poly-atomic gases works as quenchers absorbing the photons.



Oxygen has a good electron capture cross-section  $\Rightarrow$  why not use CO<sub>2</sub>

#### CF4 is a good quenching gas

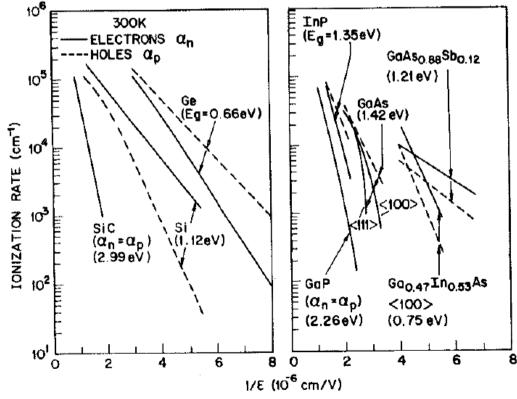


## Charge multiplication in solid state sensors (Si, Ge, GaAs etc)

• Avalanche breakdown may occur in semiconductor sensors when the kinetic energy of electrons/holes between collisions acquired by the electric field is sufficient to trigger multiplication process.

• As for the gaseous detectors the probability to initiate an avalanche depends not only on electric field strength but also on the extent of the high field region

• Avalanche breakdown is an unwanted effect in most semiconductor sensors (avalanche photo diodes and silicon multipliers are based on this effect)

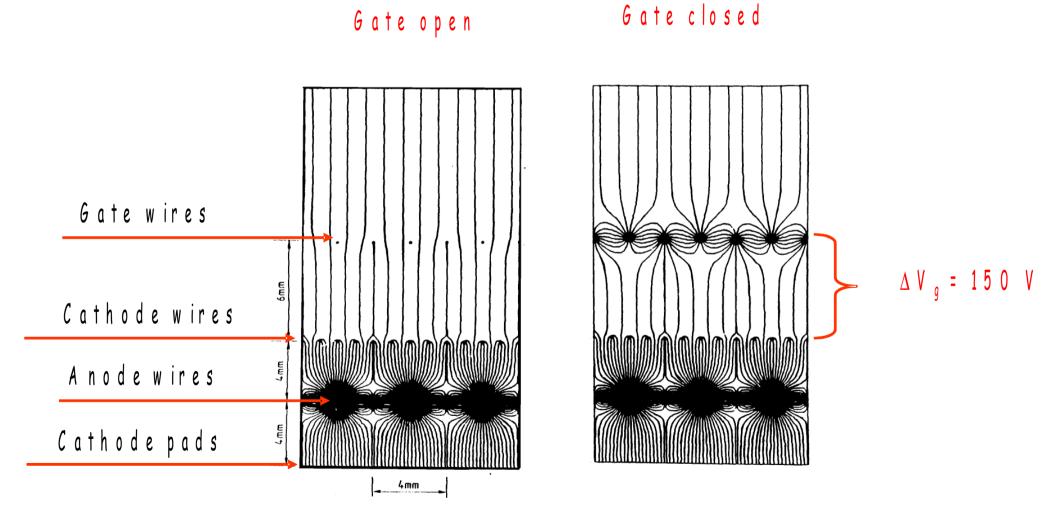


After Sze, S.M. "Physics of semiconductor devices". Wiley

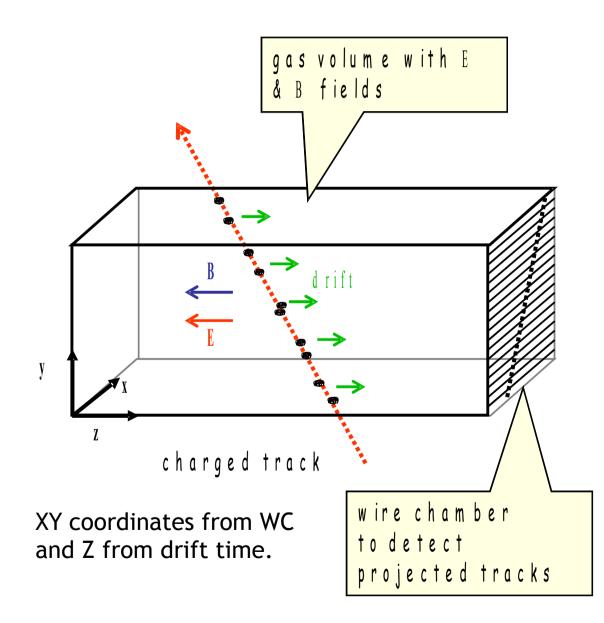
# And now some more realistic gaseous detector designs .....

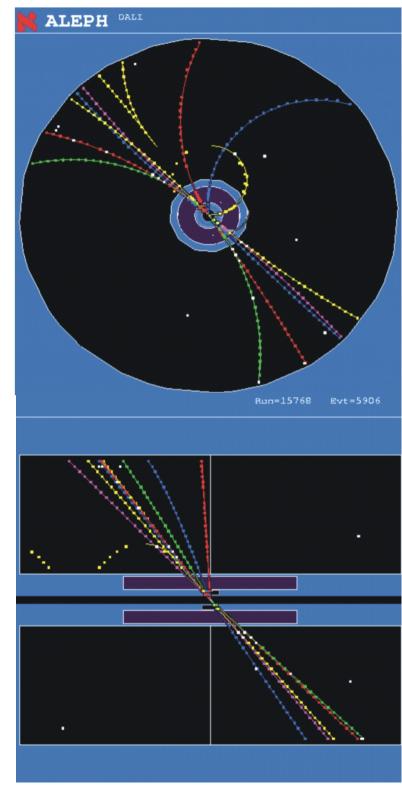
1: Split the drift chamber in a low field drift volume and a high field amplification volume

2: To control and reduce the drift time and accumulated space charge of of slow positive ions one may use gating techniques.



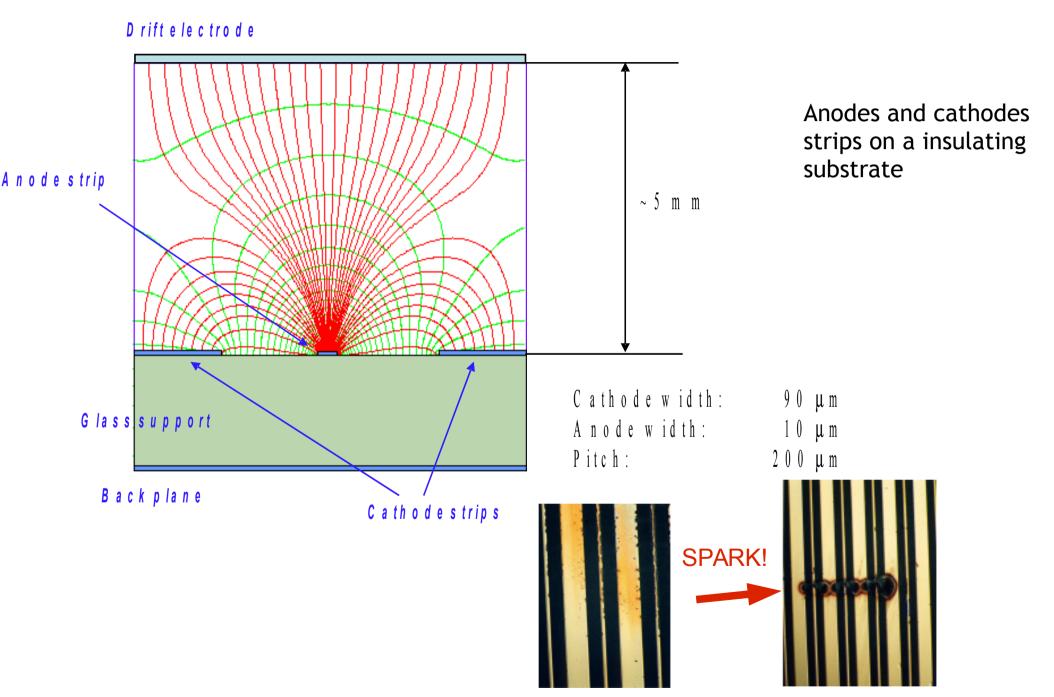
The **Time Projection Chamber (TPC)** is the **ultimate** tracking detector giving 3D space points (and dE/dx) for track reconstruction and adding little mass in tracking volume keeping multiple scattering small.



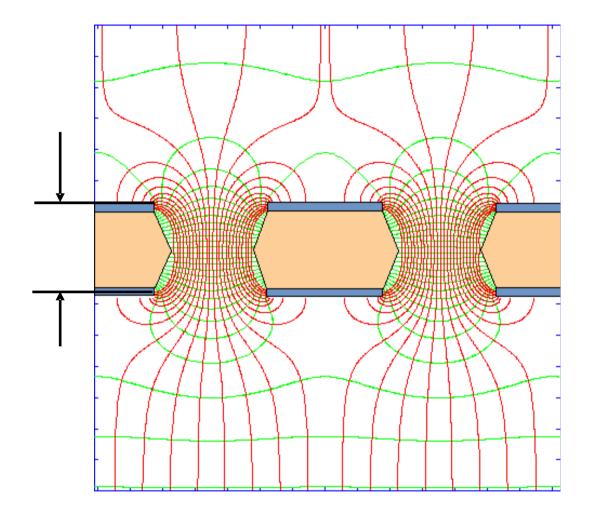


## High resolution gaseous detectors for tracking are:

• Micro-Strip Gas Chambers (MSGC), baseline technology for outer tracker in CMS TDR



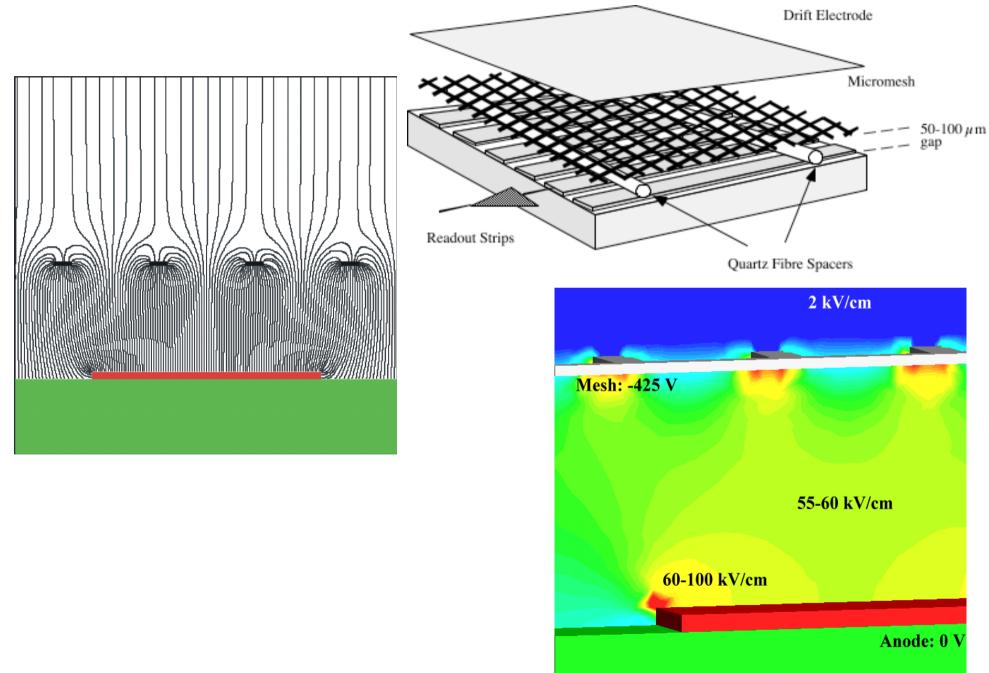
#### •Gas Electron Multiplier (GEM) [used in TOTEM]



Thin kapton foil pierced with holes. The foil is metallised on both sides and a potential difference between the two sides gives an amplification of electrons up 1000 when traversing the hole in most common gases.

Thickness:	~50 µm
ΔV:	400 - 600 V
Hole Diameter:	~ 70 µm
Pitch:	~140 µm

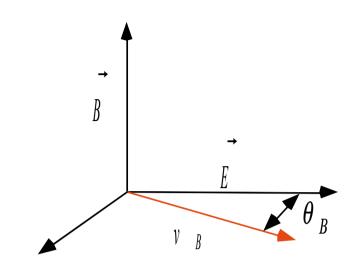
• MICROMEGAS-thin gap parallel plate chamber [candidate technology for ATLAS small forward muon wheels in phase I upgrade]



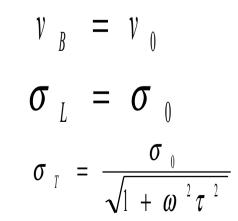
# END LECTURE

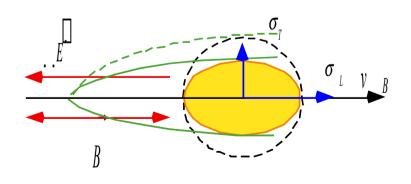
Detector in magnetic field:

 $\tan \theta_{B} = \omega \tau$   $v_{B} = v_{0} \frac{1 + \omega \tau}{1 + \omega^{2} \tau^{2}}$ 

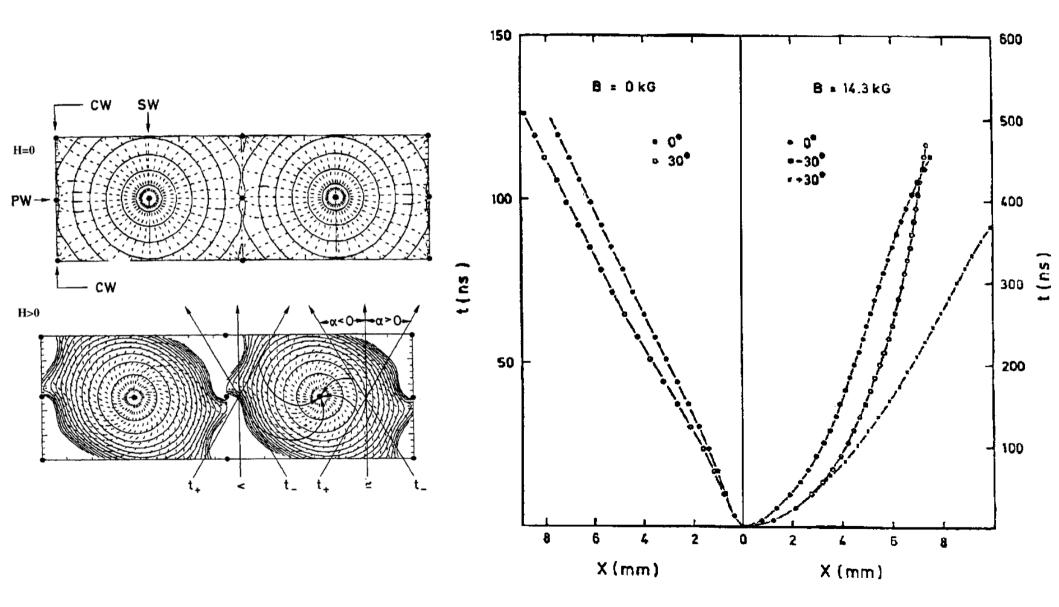


au : mean collision time  $\omega = eB/m$  Larmor frequency





### Magnetic field distortion of electric field in drift chambers



 $\Rightarrow$ The magnetic field will distort the position of the collected charge (cluster)